Amendments to the Specification:

Please replace the paragraph beginning at page 3, line 21 as with the following amended paragraph:

In order to avoid the problem above, it is important to hold the gate voltage securely. Increasing the capacity of the **[[capacitor]]** storage capacitor can be one of measures for holding the gate voltage securely. However, when the **[[capacitor]]** storage capacitor is increased, the aperture ratio is lowered to reduce the area of a pixel where light emission is actually obtained (area of effective light emission). The term area of effective light emission refers to the area of a region in which light emitted from an OLED is not blocked by objects that do not transmit light, such as a TFT and wiring line formed on the substrate.

Please replace the paragraph beginning at page 3, line 28 as with the following amended paragraph:

In recent years in particular, demands for images of higher definition are increasing and how to solve the problem of lowered aperture ratio which accompanies enhancement of pixel definition is becoming ever important. Accordingly, increasing the area that a **[[capacitor]]** storage capacitor occupies in a pixel is not desirable.

Please replace the paragraph beginning at page 4, line 8 as with the following amended paragraph:

In order to attain the above object, the present invention uses a connection wiring line, an insulating film, and a capacitance wiring line to form a **[[capacitor]]** storage capacitor. The connection wiring line is formed over a gate electrode and an active layer of a TFT of a pixel, and is connected to the active layer. The insulating film is formed on the connection wiring line. The capacitance wiring line is formed on the insulating film. Alternatively, the capacitance wiring line may be formed on the same interlayer insulating film on which a pixel electrode is formed. In this case, the capacitance wiring line and the pixel electrode may be formed from the same conductive film. A power supply line may double as the capacitance wiring line.

Please replace the paragraph beginning at page 4, line 17 as with the following amended paragraph:

This structure enables the **[[capacitor]]** storage capacitor to overlap the TFT, thereby increasing the capacity of the **[[capacitor]]** storage capacitor while keeping the aperture ratio from lowering. Accordingly, a change in gate voltage due to leakage or other causes can be controlled to prevent a change in luminance of an OLED and flickering of screen in analog driving.

Please replace the paragraph beginning at page 6, line 13 as with the following amended paragraph:

A region that has one of source lines (S), one of gate lines (G), and one of power supply lines (V) corresponds to a pixel 100. Each pixel has a switching TFT 101, a driving TFT 102, an OLED 103, and a **[[capacitor]]** storage capacitor 104.

Please replace the paragraph beginning at page 6, line 30 as with the following amended paragraph:

Of two electrodes that the **[[capacitor]]** storage capacitor has, one is electrically connected to the gate electrode of the driving TFT 102 and the other is electrically connected to the power supply line (V).

Please replace the paragraph beginning at page 7, line 3 as with the following amended paragraph:

Next, a specific structure of the **[[capacitor]]** storage capacitor in the light emitting device of the present invention will be described with reference to Fig. 2. Denoted by 101 and 102 are a switching TFT and a driving TFT, respectively. The TFTs are formed on an insulating surface.

Please replace the paragraph beginning at page 8, line 12 as with the following amended paragraph:

In the present invention, the **[[capacitor]]** storage capacitor 104 is formed in an area where the third interlayer insulating film 120 is sandwiched between the connection wiring line 118 and the capacitance wiring line 121. The capacitance wiring 121 can be formed from the same conductive film as the pixel electrode 122 and, therefore, the **[[capacitor]]** storage capacitor can be formed without increasing the number of steps in manufacture process. The **[[capacitor]]** storage capacitor 104 is formed to overlap the active layer 130 of the switching TFT 101, which makes it possible to obtain a **[[capacitor]]** storage capacitor without reducing the aperture ratio.

Please replace the paragraph beginning at page 8, line 28 as with the following amended paragraph:

In the present invention, structures of the TFTs are not limited to those shown in Fig. 2. Also, the present invention may have, in addition to the **[[capacitor]]** storage capacitor 104 that is formed from the connection wiring line 118 and the capacitance wiring line 121, a **[[capacitor]]** storage capacitor of different structure.

Please replace the paragraph beginning at page 9, line 12 as with the following amended paragraph:

This embodiment m ode shows a case in which a pixel has two TFTs. However, the present invention is not limited thereto. A **[[capacitor]]** storage capacitor structured in accordance with the present invention can be formed irrespective of how many TFTs one pixel has. The **[[capacitor]]** storage capacitor of the present invention can be obtained as long as it is formed from: a wiring line (connection wiring line) that is formed over a gate electrode and an active layer of a TFT of a pixel and is connected to the active layer; an insulating film formed on the connection wiring line; and a wiring line (capacitance formed on the insulating film.

Please replace the paragraph beginning at page 9, line 20 as with the following amended paragraph:

With the above structure, the present invention can make the **[[capacitor]]** storage capacitor overlap the TFT and therefore can increase the capacity of the **[[capacitor]]** storage capacitor while keeping the aperture ratio from lowering. Accordingly, a change in gate voltage due to leakage or other causes can be avoided to thereby prevent a change in luminance of the OLED and flickering of screen in analog driving.

Please replace the paragraph beginning at page 17, line 4 as with the following amended paragraph:

The capacitance wiring line 235 overlaps the connection wiring line 229 with the third interlayer insulating film 233 interposed therebetween. In the present invention, a **[[capacitor]]** storage capacitor 236 is formed from the capacitance wiring line 235, the third interlayer insulating film 233, and the connection wiring line 229.

Please replace the paragraph beginning at page 17, line 11 as with the following amended paragraph:

Though not shown in Fig. 7A, the capacitance wiring 235 that constitutes the **[[capacitor]]** storage capacitor 236 is connected to the capacitance wiring line 235 of the adjacent pixel. Fig. 9 shows how a plurality of pixels, each structured as illustrated in Fig. 8, are arranged.

Please replace the paragraph beginning at page 18, line 30 as with the following amended paragraph:

In this embodiment, a **[[capacitor]]** storage capacitor 243 is formed from the impurity region 209, the gate insulating film 205, and the capacitance electrode 213. A **[[capacitor]]** storage capacitor 244 is formed from the capacitance electrode 213, the second interlayer insulating film 227, and the power supply line 231. The impurity region 209 and the capacitance

electrode 213 overlap the power supply line 231 and, therefore, the ~~capacitor storages~~ storage capacitors 243 and 244 can be formed without lowering the aperture ratio.

Please replace the paragraph beginning at page 19, line 18 as with the following amended paragraph:

This embodiment describes a **[[capacitor]]** storage capacitor of the present invention which has a structure different from the one in Fig. 7A.

Please replace the paragraph beginning at page 20, line 5 as with the following amended paragraph:

On the surface of the conductive layer, an insulating film 310 is formed by anodization or plasma oxidization (anodization, in this embodiment) to have a thickness of 20 to 100 nm (preferably 30 to 50 nm). The insulating film serves as dielectric. In this embodiment, the connection wiring line 305 is a laminate of a film mainly containing aluminum and a film mainly containing titanium, and the film mainly containing aluminum is anodized to form an aluminum oxide film (alumina film) that is an anodized film. The anodized film in this embodiment corresponds to the insulating film 310, and is used as the dielectric of the **[[capacitor]]** storage capacitor. An insulating oxide film obtained by anodization of a tantalum (Ta) film or a titanium (Ti) film also has high dielectric constant and therefore is suitable as the dielectric of the **[[capacitor]]** storage capacitor.

Please replace the paragraph beginning at page 22, line 1 as with the following amended paragraph:

In this embodiment, a **[[capacitor]]** storage capacitor 324 is formed from the connection wiring line 305, the insulating film 310 that is in contact with the connection wiring line 305, and the capacitance wiring line 322.

Please replace the paragraph beginning at page 22, line 4 as with the following amended paragraph:

The **[[capacitor]]** storage capacitor structured in accordance with this embodiment has wider choices for the thickness of dielectric and for the dielectric constant than the one in Embodiment 1.

Please replace the paragraph beginning at page 22, line 14 as with the following amended paragraph:

The source line 303 and the power supply line 304 are formed on a gate insulating film 307 at the same time a gate electrode 305 of the switching TFT 301 and a gate electrode 306 of the driving TFT 302 are formed. A capacitance electrode 304 overlaps an impurity region 308 with the gate insulating film 307 interposed therebetween. The capacitance electrode 304, the gate insulating film 307, and the impurity region 308 constitute a **[[capacitor]]** storage capacitor 309.

Please replace the paragraph beginning at page 23, line 17 as with the following amended paragraph:

A **[[capacitor]]** storage capacitor 343 that is the feature of the present invention is formed from the connection wiring line 312, the third interlayer insulating film 340, and the capacitance wiring line 341.

Please replace the paragraph beginning at page 25, line 17 as with the following amended paragraph:

Fig. 14 is a circuit diagram of a pixel portion in a light emitting device of the present invention. Reference symbol 601 denotes a switching TFT, 602, a driving TFT, 603, an OLED, and 604, a **[[capacitor]]** storage capacitor. Details about connection structure in the pixel are the same as those in the pixel shown in Fig. 1.

Please replace the paragraph beginning at page 27, line 4 as with the following amended paragraph:

In analog driving, the capacity of a **[[capacitor]]** storage capacitor is desirably larger than in digital driving. Therefore, the structure of the light emitting device of the present invention, in which the **[[capacitor]]** storage capacitor can have a large capacity while avoiding lowering of the aperture ratio, is suitable for analog driving. However, the present invention is not limited to this driving method and the present invention can fully be applied to a digitally-driven light emitting device.

Please replace the paragraph beginning at page 31, line 3 as with the following amended paragraph:

In this embodiment, the n-channel TFT or the p-channel TFT that constitutes the driving circuit TFT 4201 is manufactured by a known method, and a p-channel TFT manufactured by a known method is used for the driving TFT 4202. The pixel portion 4002 is provided with a **[[capacitor]]** storage capacitor (not shown) connected to a gate of the driving TFT 4202.

Please replace the paragraph beginning at page 35, line 8 as with the following amended paragraph:

This embodiment describes a **[[capacitor]]** storage capacitor of the present invention which has a structure different from the one shown in Fig. 2.

Please replace the paragraph beginning at page 36, line 9 as with the following amended paragraph:

In this embodiment, the **[[capacitor]]** storage capacitor 104 is formed in an area where the capacitance insulating film 170 is sandwiched between the connection wiring line 118 and the capacitance wiring line 121. The capacitance insulating film 170 is described in this embodiment as a layer separate from the third interlayer insulating film 120. However, the

capacitance insulating film 170 may be regarded as a part of the third interlayer insulating film 120 that is comprised of layers of insulating films.

Please replace the paragraph beginning at page 38, line 4 as with the following amended paragraph:

With the above structure, the present invention allows the **[[capacitor]]** storage capacitor to overlap the TFT, thereby increasing the capacity of the **[[capacitor]]** storage capacitor while keeping the aperture ratio from lowering. Accordingly, a change in gate voltage due to leakage or other causes can be avoided to prevent a change in luminance of an OLED and flickering of screen in analog driving.